



The World Leader in High-Performance Signal Processing Solutions

RF Power Amplifiers

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Outline

- ◆ **PA Introduction**
 - **Power transfer characteristics**
 - **Intrinsic PA metrics**
 - **Linear and Non-linear amplifiers**
 - **PA Architectures**
- ◆ **Single-Stage Linear PA**
 - **Load-line theory**
 - **Transistors size**
 - **Input and Output Matching**
 - **So why is this so hard?**
- ◆ **High-efficiency PAs**
 - **Class A, AB, B and C amplifiers**



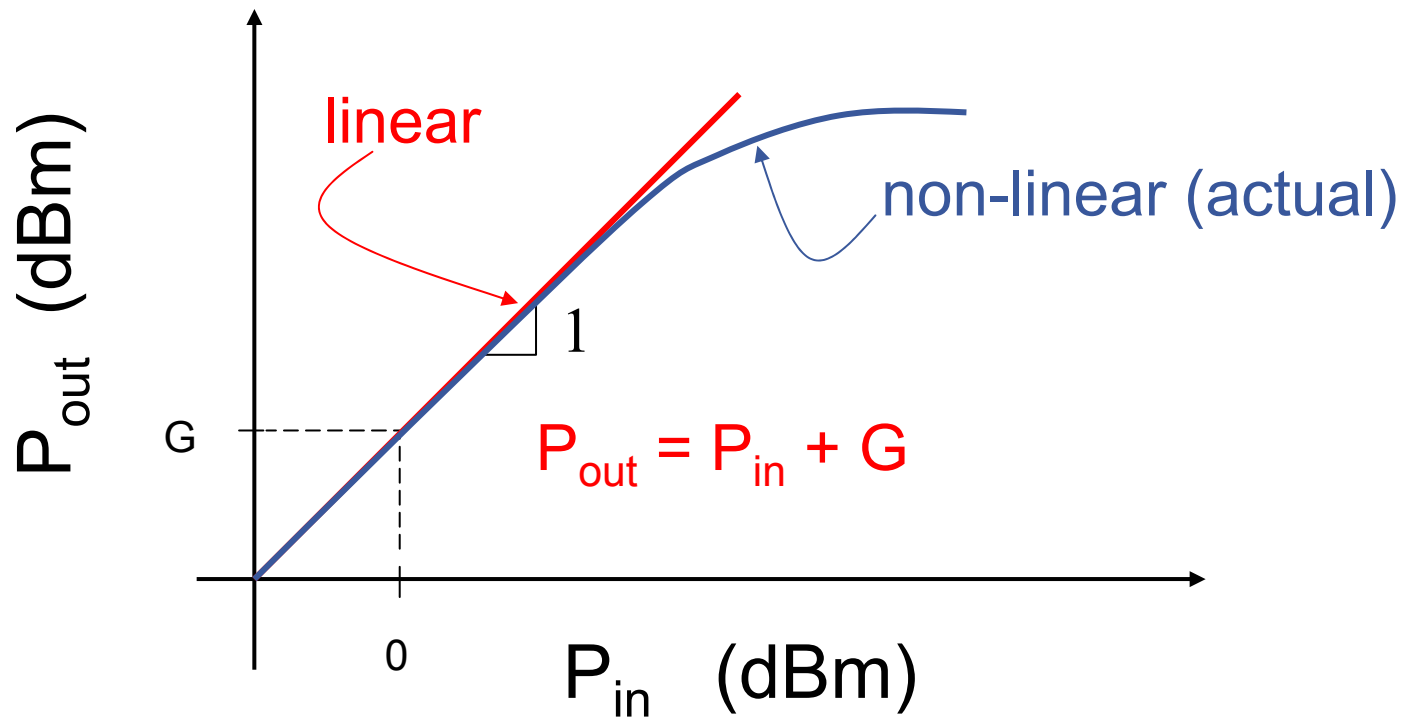
Outline (cont.)

- ◆ **Real-World Design Example**
 - **Selecting architecture, number of stages**
 - **Designing stages**
 - **Tuning: inter-stage match and output**
- ◆ **System specifications**
 - **Ruggedness: load mis-match and VSWR**
 - **Linearity: spectral mask (ACPR), switching transients**
 - **Noise in receive band**
- ◆ **Power Control**



PA Transfer characteristics

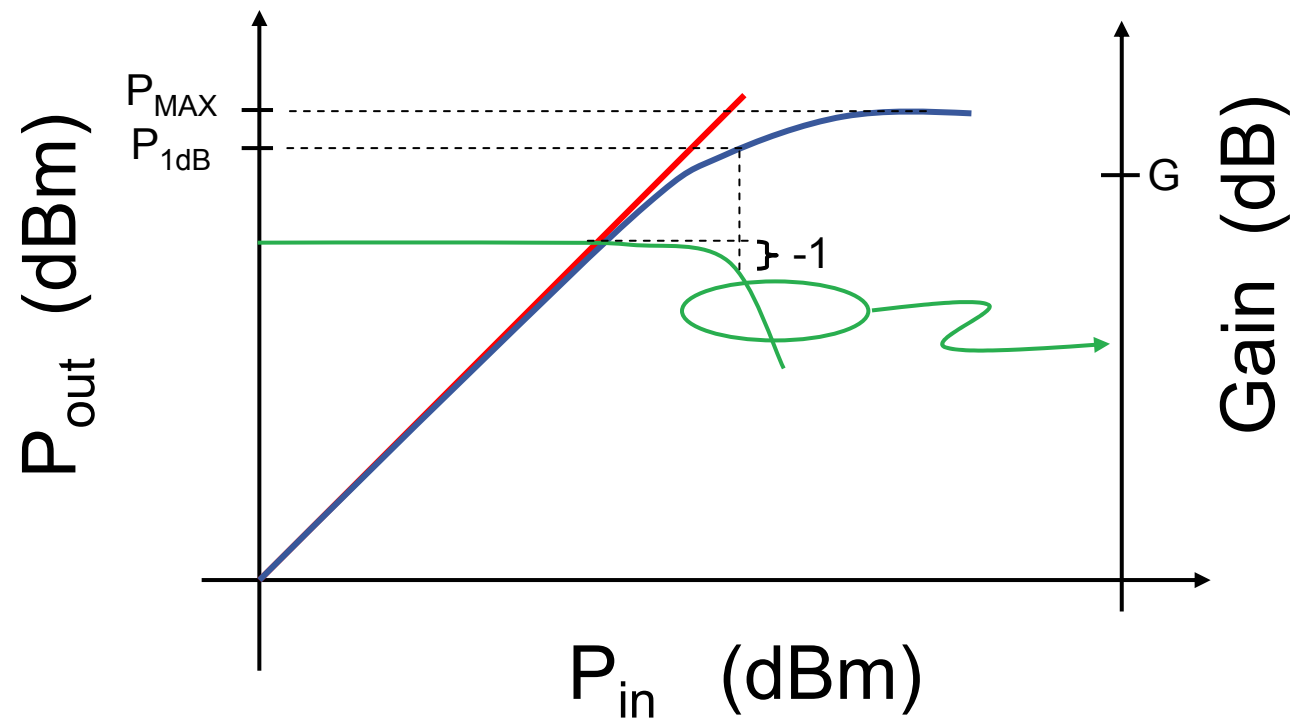
Defining linearity:





PA Transfer characteristics

Defining linearity:





PA Introduction: Intrinsic PA Metrics

- ◆ **P_{1dB}** : Output power at which linear gain has compressed by 1dB (measure of linear power handling)
- ◆ **P_{MAX}** : Maximum output power (saturated power)
- ◆ **Gain**: Generally taken to mean transducer gain

$$\frac{\text{Power delivered to load}}{\text{Power available from source}}$$

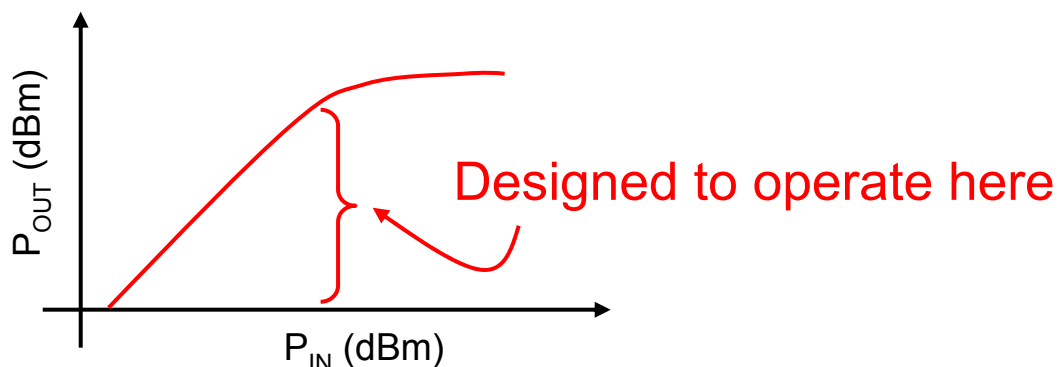
- ◆ **PAE: Power-added Efficiency**

$$\frac{\text{Power to load} - \text{Power from source}}{\text{Power from supply}}$$



Linear and Non-linear PAs

- ◆ “Linear PA” generally refers to a PA which operates at constant gain, needs to preserve amplitude information

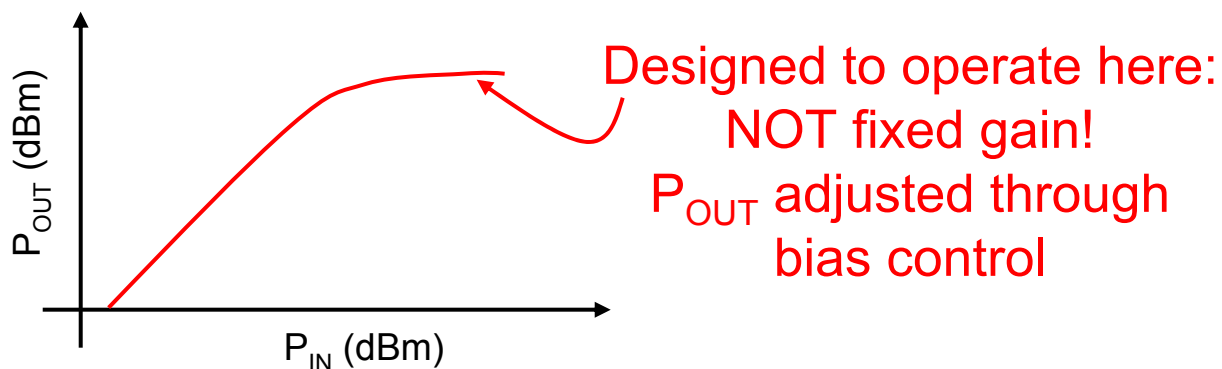


- ◆ Not necessarily class A (will discuss later ...) Peak efficiencies often only 40 to 45 %
- ◆ Useful for modulation schemes with amplitude modulation (QPSK, 8-PSK, QAM)



Linear and Non-linear PAs

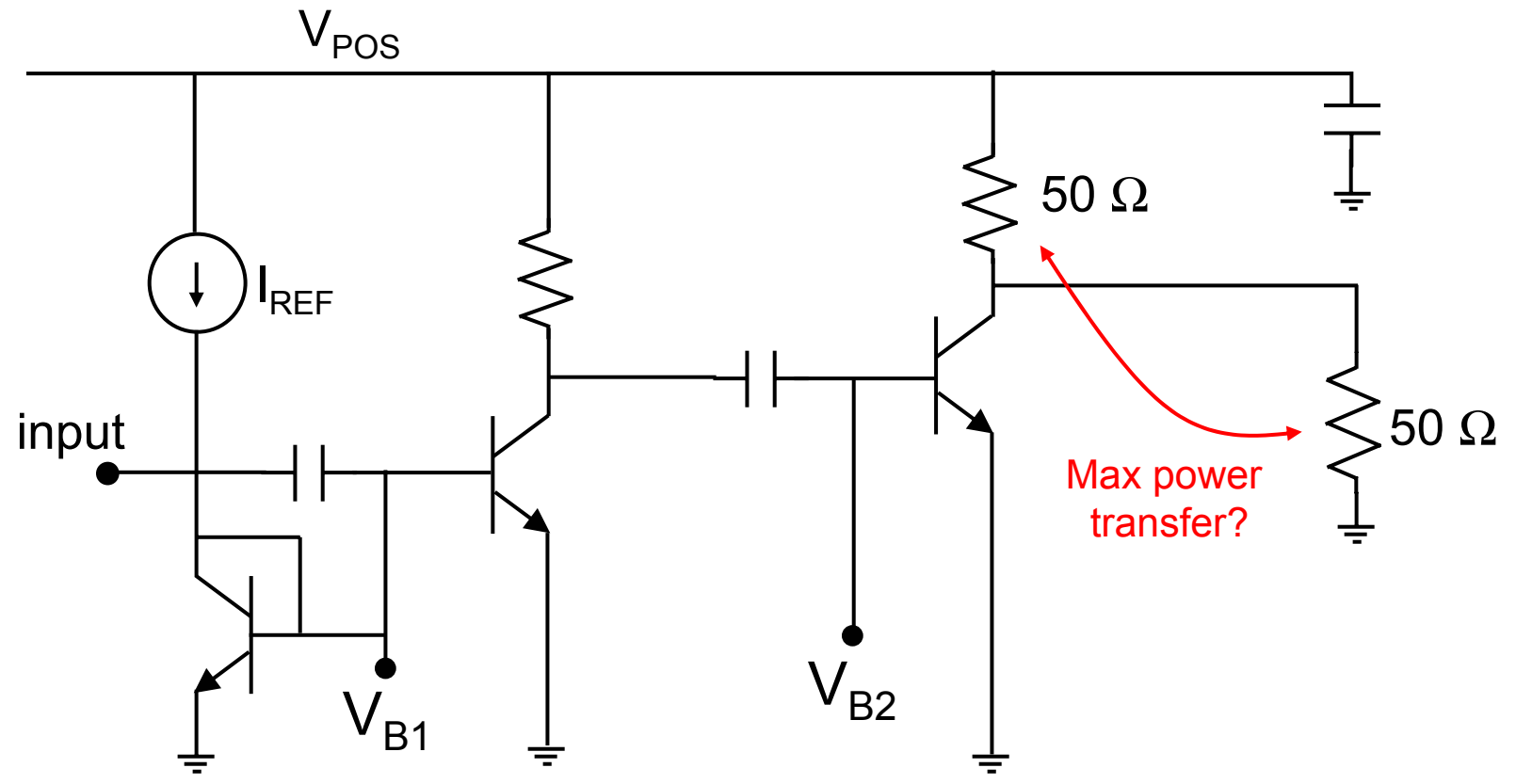
- ◆ “Non-linear PA” generally refers to a PA designed to operate with constant P_{IN} , output power varies by changing gain



- ◆ Operation in saturated mode leads to high peak efficiencies $> 50\%$; “backed-off” efficiencies drop quickly
- ◆ Useful for constant-envelope modulation schemes (GMSK)

PA Architectures

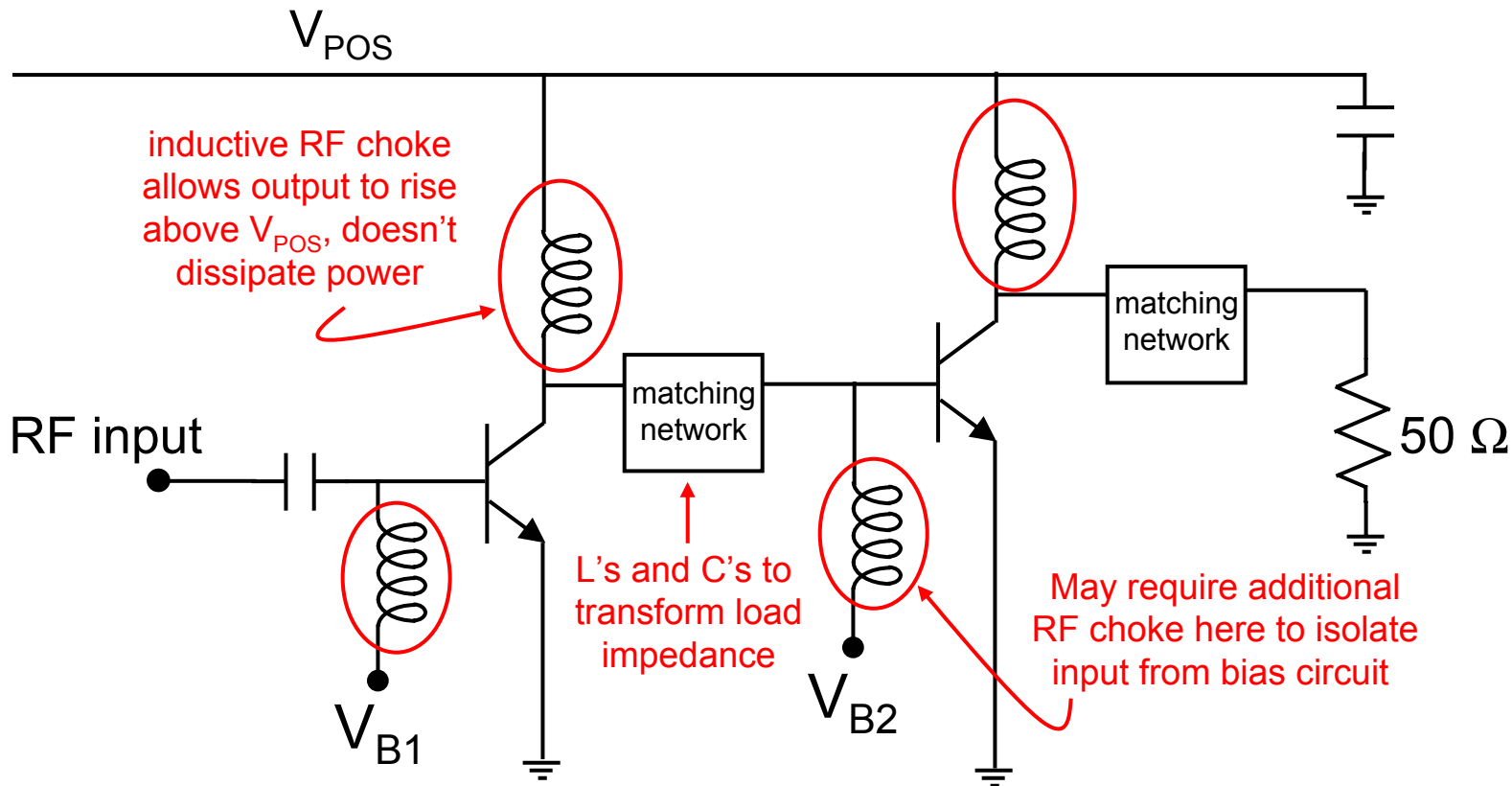
Typical 2-stage (6.012) design





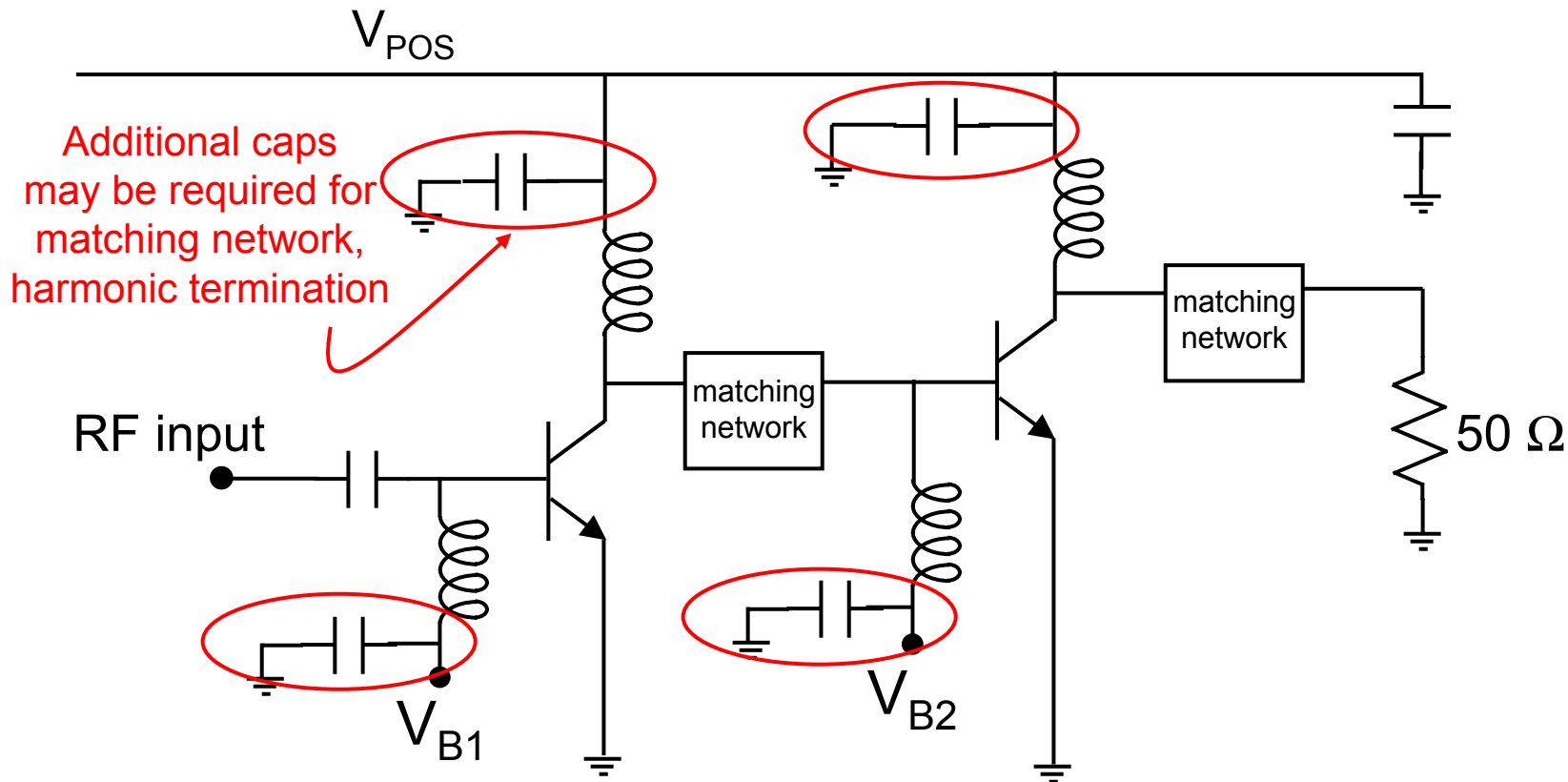
PA Architectures

Typical 2-stage RF PA design



PA Architectures

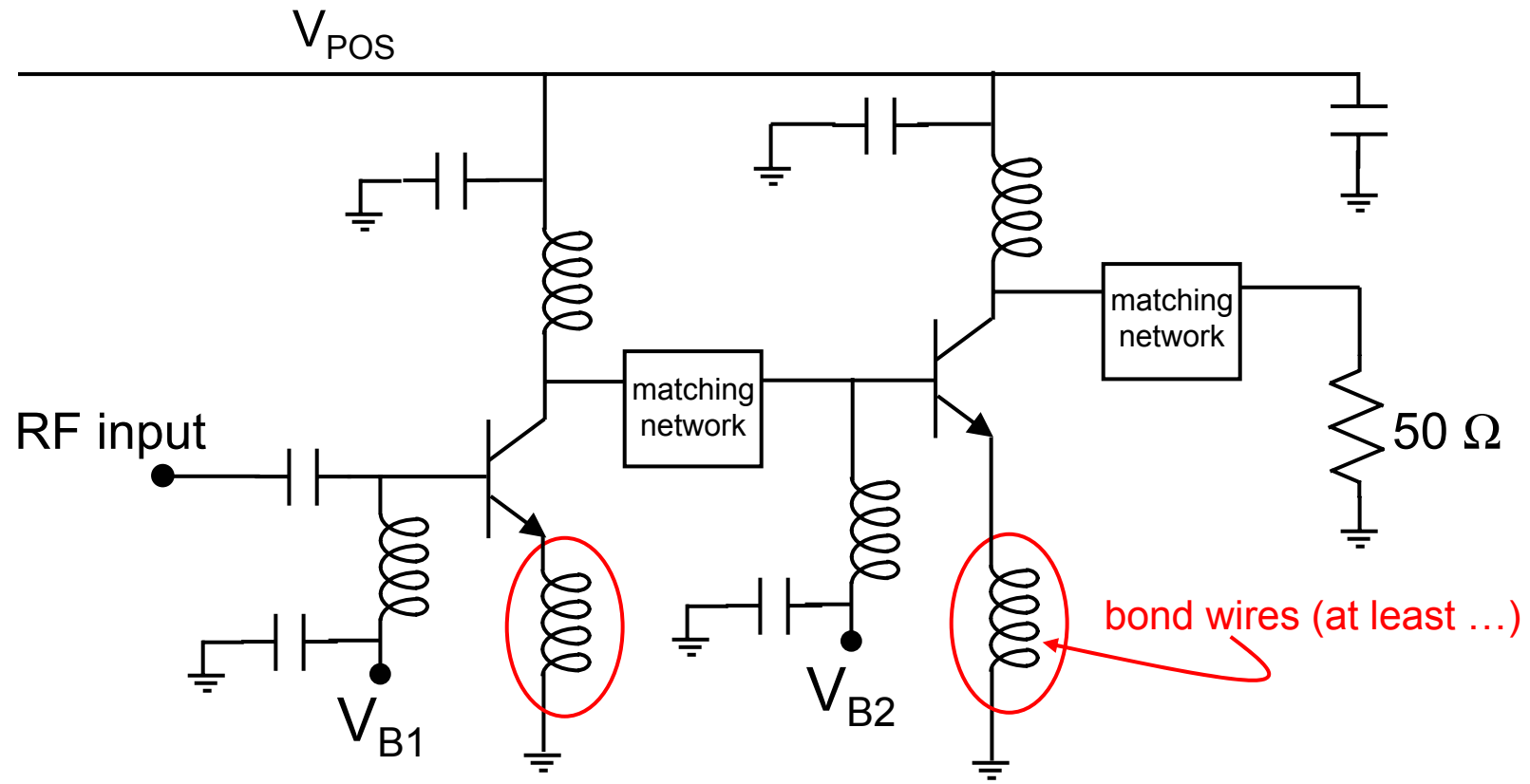
Typical 2-stage RF PA design





PA Architectures

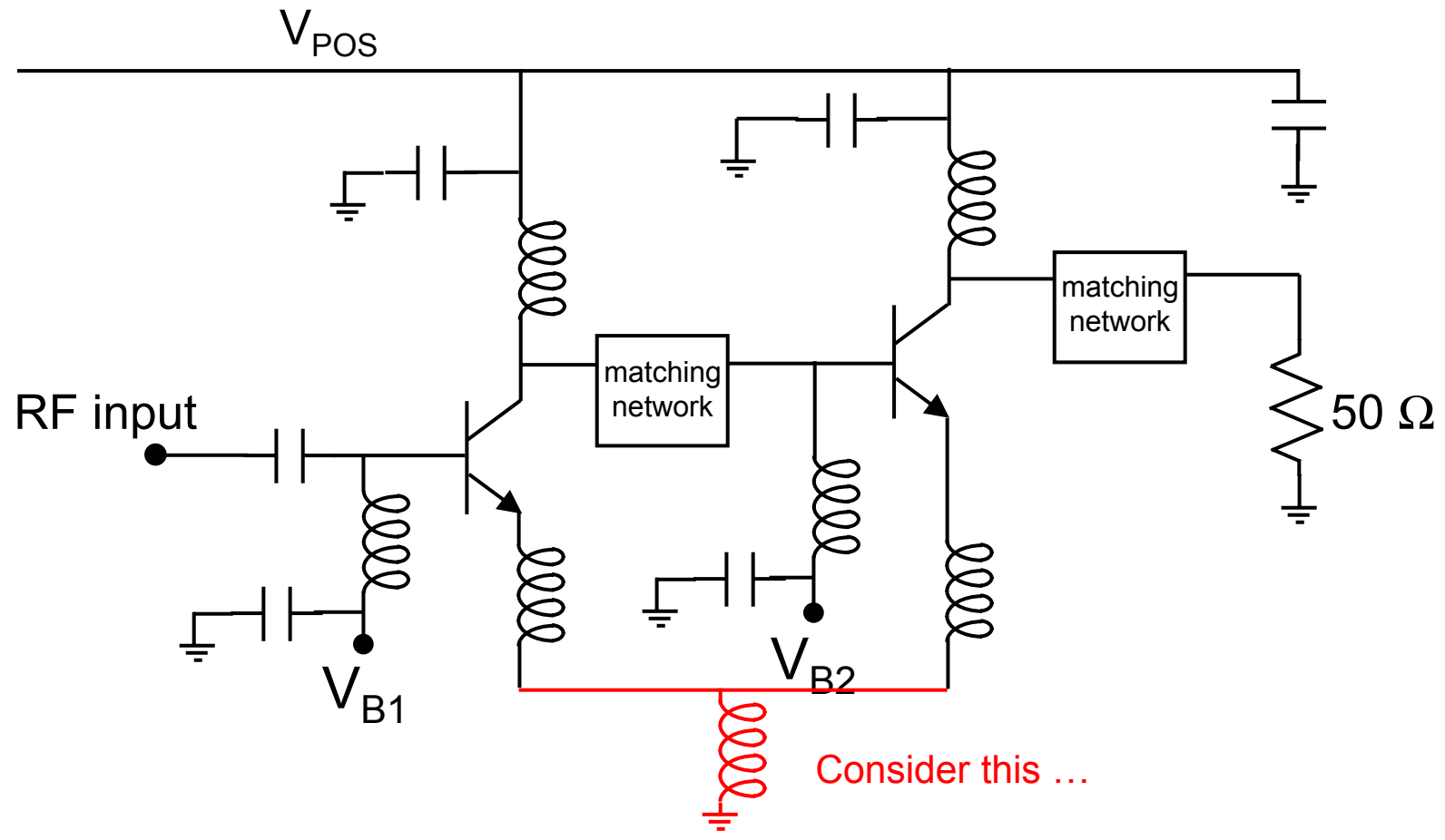
Typical 2-stage RF PA design





PA Architectures

Typical 2-stage RF PA design





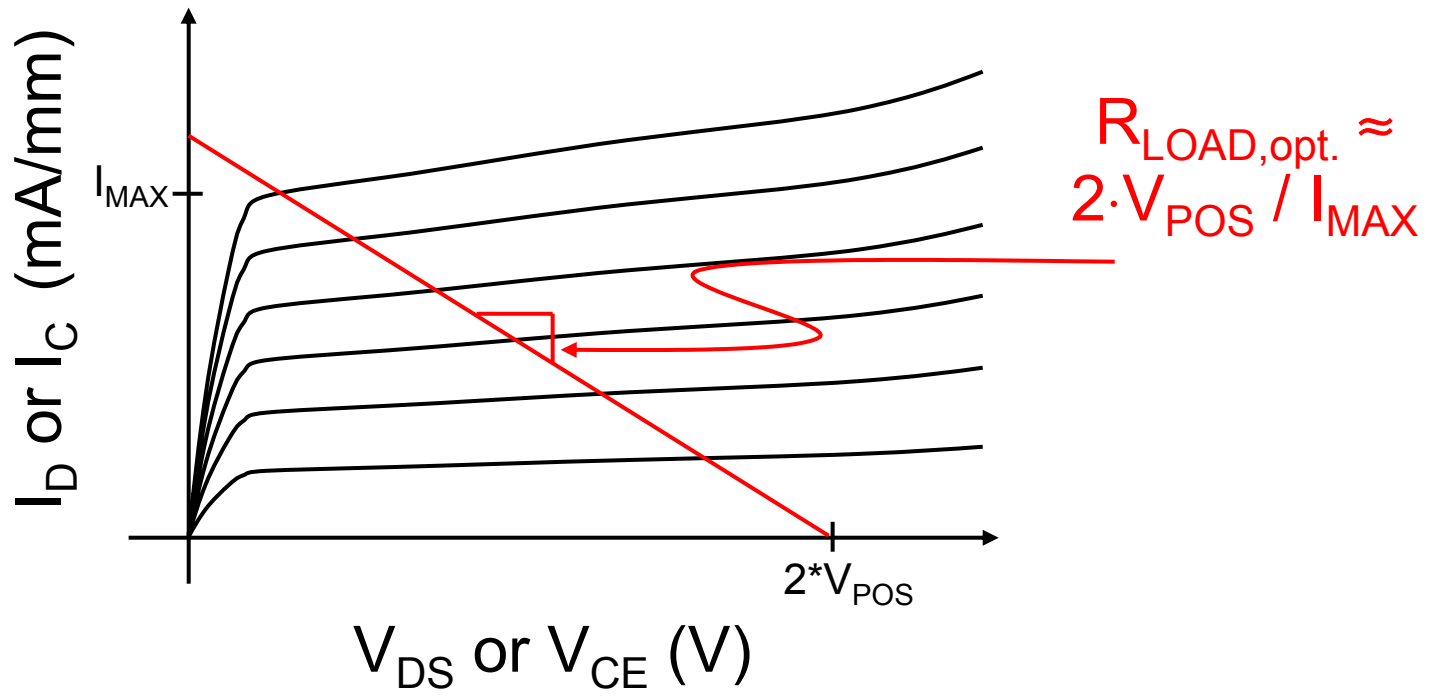
PA Architectures

- ◆ “Gain stage” is one transistor with passive elements
- ◆ “Active” components often limited to 2 or 3 transistors (gain stages) in signal path
- ◆ Transistor design very important!
 - Many parallel transistors – often look like mini-circuits themselves
- ◆ Passive components just as important as transistors!
 - Circuits must be tunable to account for uncertainties in determining values *a priori* (i.e. simulations stink – especially large-signal, RF simulations)
 - Q and parasitic elements of passives important



Single-Stage Linear PA

- ◆ **Load-line theory:** the maximum power that a given transistor can deliver is determined by the power supply voltage and the maximum current of the transistor

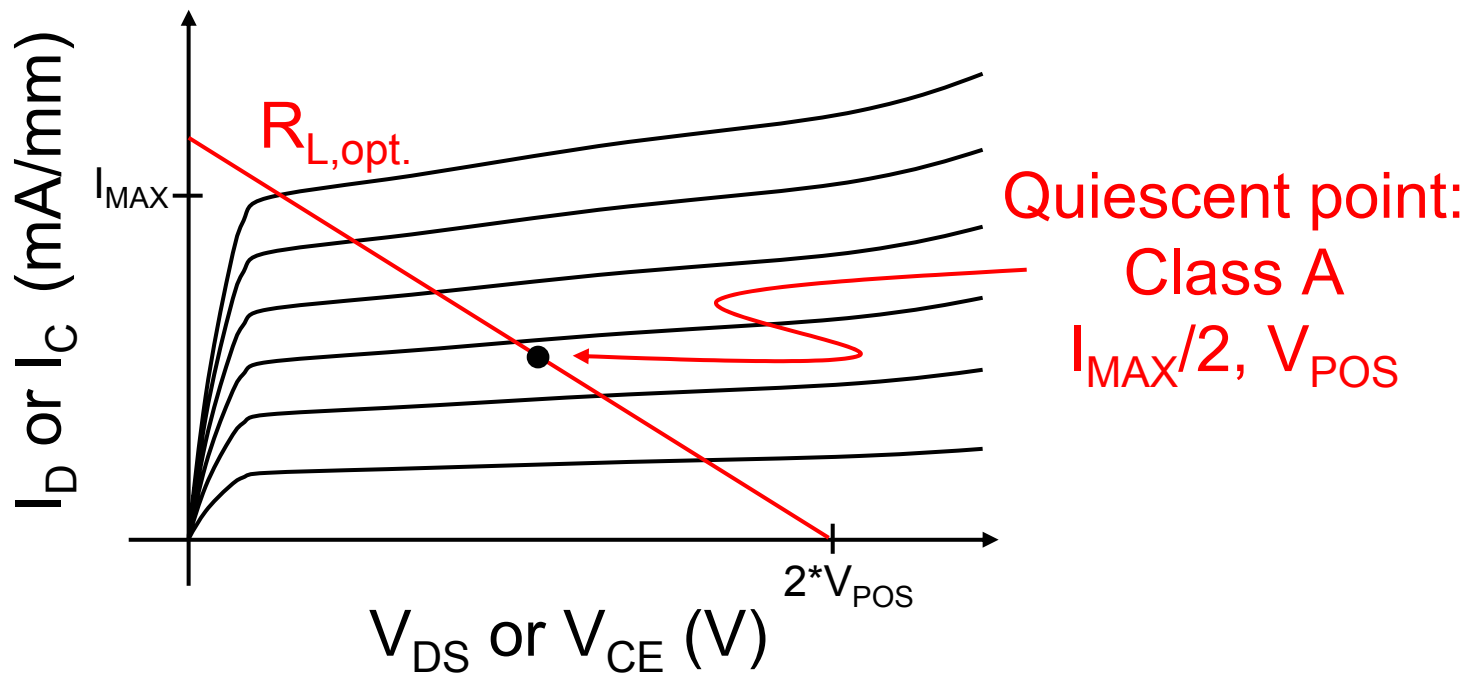




Single-Stage Linear PA

- ◆ Transistor size chosen to deliver required output power

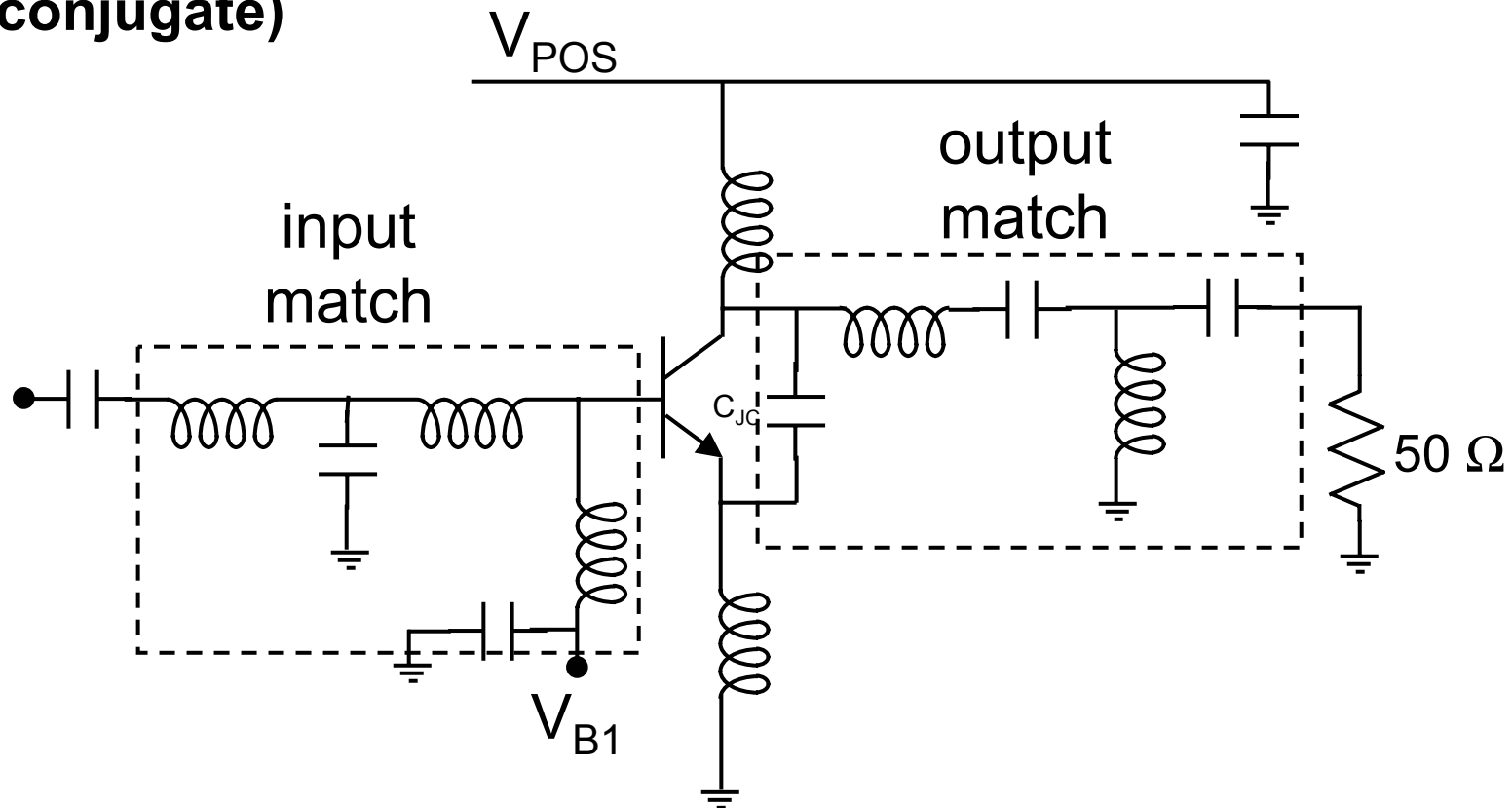
$$P_{\text{OUT}} \approx I_{\text{MAX}} \cdot V_{\text{POS}} / 4$$





Single-Stage, Linear PA

- ◆ Design output match to transform 50Ω load to $R_{L,opt}$ at transistor output; then design input match for gain (complex conjugate)





Seems simple, so why is this so hard?

- ◆ **Determining I_{MAX} is not so easy**
 - For BJTs, one reference suggested that “the best way of estimating its value is to build an optimized class A amplifier and observe the dc supply current.”¹
 - Somewhat easier for depletion-mode GaAs FETs – I_{MAX} often corresponds to $V_{GS} = 0V$
 - Values don’t scale linearly with transistor size
- ◆ **Optimal load resistance only a theoretical number**
 - Transmission line effects, parasitic L’s and C’s significant at RF
 - Common practice is to vary the load of an actual transistor to determine the peak output power: the load-pull measurement
(Noticing a distinct pattern of “empirical” design emerging?)

¹ RF Power Amplifiers for Wireless Communications, Steve Cripps, Artech House, Boston, 1999.



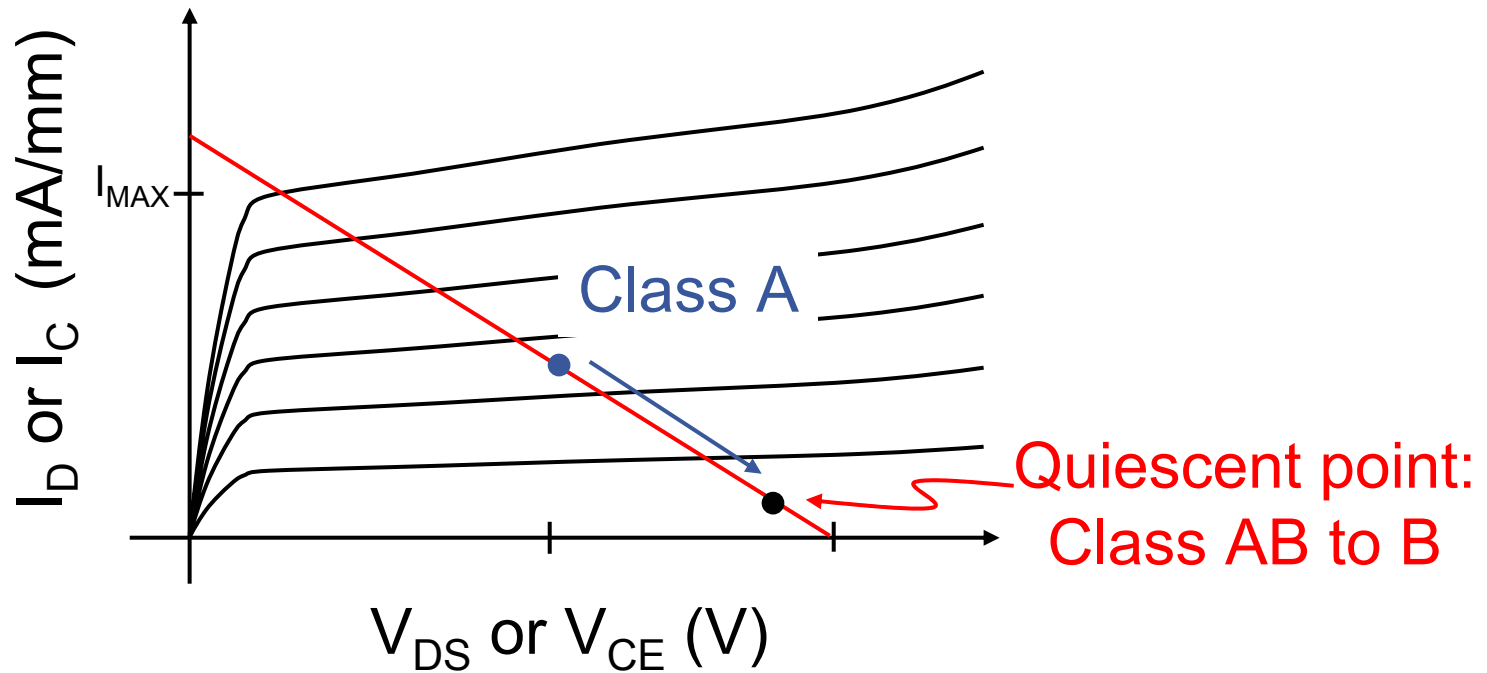
Seems simple, so why is this so hard?

- ◆ **Now consider the problem for multiple stages ... double the trouble**
 - Typical single-stage gain only 10 – 15 dB
 - Inter-stage match now required to match input impedance of 2nd stage to desired output impedance of 1st stage.
- ◆ **Problems with matching circuits:**
 - Large matching ratios → high Q circuits for simple L matches
 - Multi-segment matches use valuable real estate, add cost
- ◆ **Transistor itself matters – a lot!**
 - Many parallel transistor
 - Ballasting, balancing and layout extremely important



High-efficiency PAs

- ◆ Input signal swing turns on transistor – conduction for only part of sinusoidal period



High-Efficiency PAs

- ◆ Assume output match will filter out non-linearities caused by discontinuous conduction:

